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(54) Title: METHOD OF MANUFACTURING SILICON NITROGENOUS FILM

(57) Abstract: A method is disclosed for the preparation of a silicon nitrogenous film. Polysilazane film is exposed to an electron beam irradiation and subsequently to at least one process selected from the group consisting of a vacuum ultra-violet light irradiation and a plasma processing. The treated film is heated under a non-oxidizing atmosphere to manufacture a silicon nitrogenous film. The silicon nitrogenous film is able to be formed at low process temperature. Further, the silicon nitrogenous film has a high refractive index and low oxygen content.



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